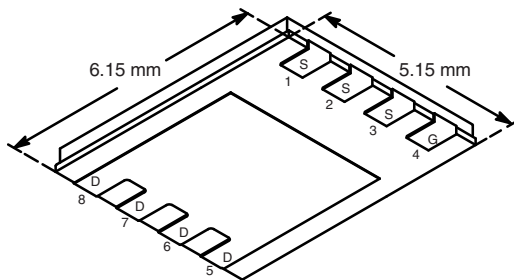


N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
30	0.0033 at $V_{GS} = 10$ V	40	37 nC
	0.0046 at $V_{GS} = 4.5$ V	40	

PowerPAK SO-8



Bottom View

Ordering Information: Si7674DP-T1-E3 (Lead (Pb)-free)
Si7674DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

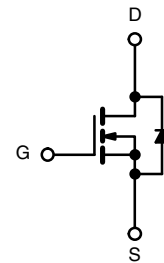
- Halogen-free According to IEC 61249-2-21 Definition
- Extremely Low Q_{gd} for Switching Losses
- 100 % R_g Tested
- 100 % Capacitance Tested
- 100 % Avalanche Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Core DC/DC in Notebooks



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	30	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	40	
		$T_C = 70$ °C	32	
		$T_A = 25$ °C	31 ^{b, c}	
		$T_A = 70$ °C	25 ^{b, c}	
Pulsed Drain Current	I_{DM}	70	A	
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C		40
		$T_A = 25$ °C		4.9 ^{b, c}
Single Pulse Avalanche Current	I_{AS}	40		mJ
Single Pulse Avalanche Energy	E_{AS}	80		
Maximum Power Dissipation	P_D	$T_C = 25$ °C	83	
		$T_C = 70$ °C	53	
		$T_A = 25$ °C	5.4 ^{b, c}	
		$T_A = 70$ °C	3.4 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	$t \leq 10$ s	R_{thJA}	18	23	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.0	1.5	

Notes:

- Based on $T_C = 25$ °C.
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- See solder profile (www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 65 °C/W.

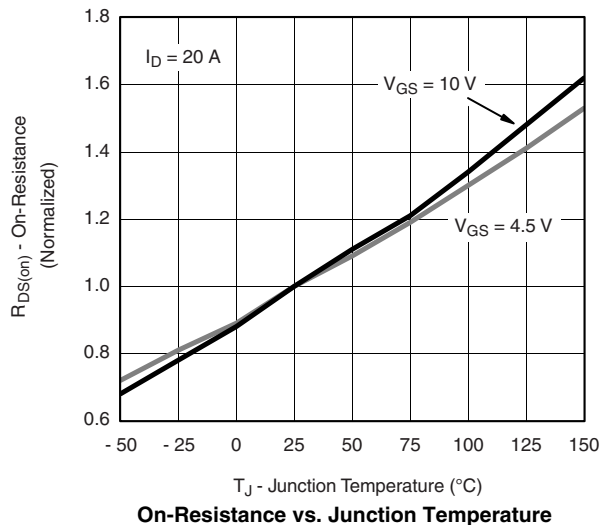
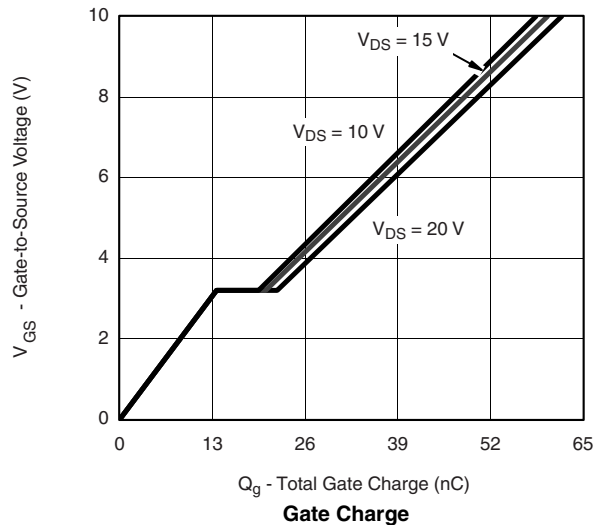
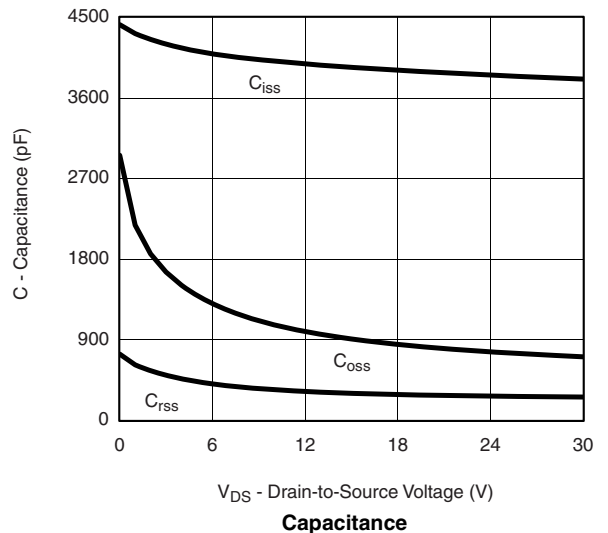
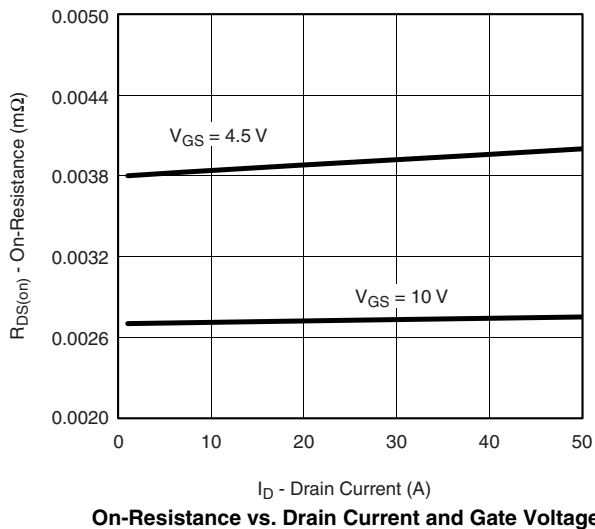
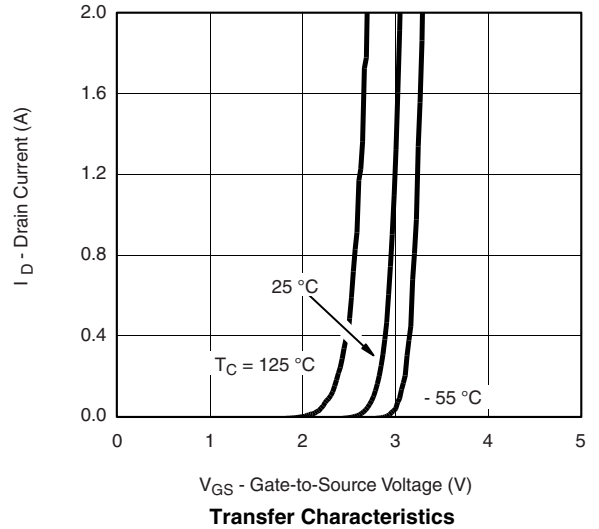
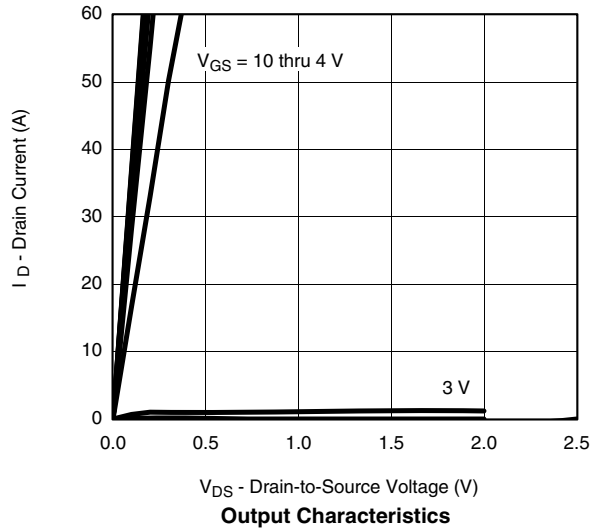
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		33		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 6.3		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		3.0	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0027	0.0033	Ω
		V _{GS} = 4.5 V, I _D = 20 A		0.0038	0.0046	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 20 A		87		S
Dynamic^b						
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		3940	5910	pF
Output Capacitance	C _{oss}			910	1365	
Reverse Transfer Capacitance	C _{rss}			305	458	
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 20 A		60	90	nC
		V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 20 A		28	42	
Gate-Source Charge	Q _{gs}			13.6		
Gate-Drain Charge	Q _{gd}		6.8			
Gate Resistance	R _g	f = 1 MHz		0.95	1.5	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω		16	25	ns
Rise Time	t _r			98	150	
Turn-Off Delay Time	t _{d(off)}			32	50	
Fall Time	t _f			8	15	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω		34	50	
Rise Time	t _r			210	315	
Turn-Off Delay Time	t _{d(off)}			26	40	
Fall Time	t _f			9	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			40	A
Pulse Diode Forward Current ^a	I _{SM}				70	
Body Diode Voltage	V _{SD}	I _S = 5 A		0.75	1.1	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C		47	70	ns
Body Diode Reverse Recovery Charge	Q _{rr}			50	80	nC
Reverse Recovery Fall Time	t _a			23		ns
Reverse Recovery Rise Time	t _b			24		

Notes:

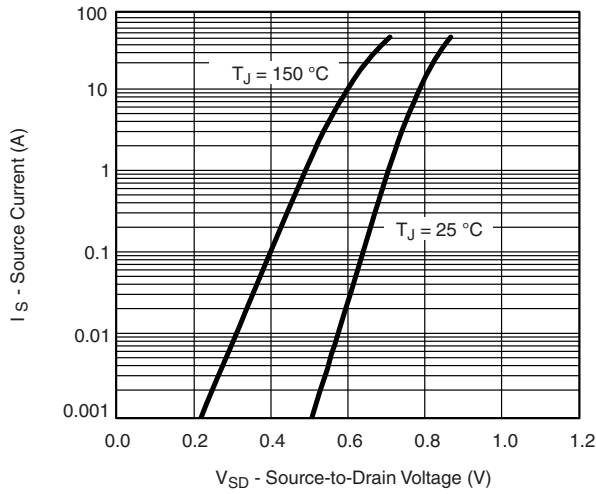
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

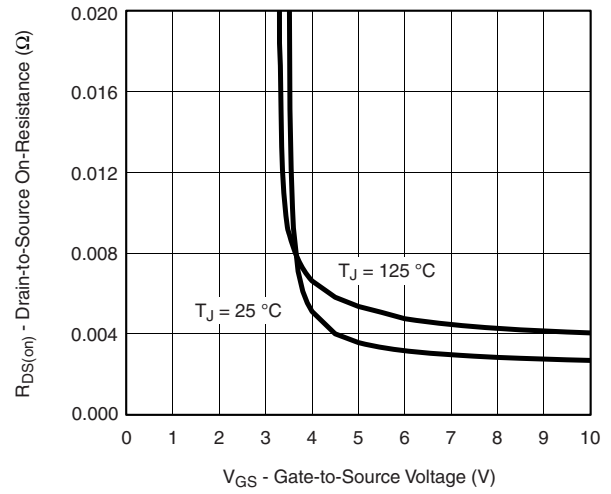
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



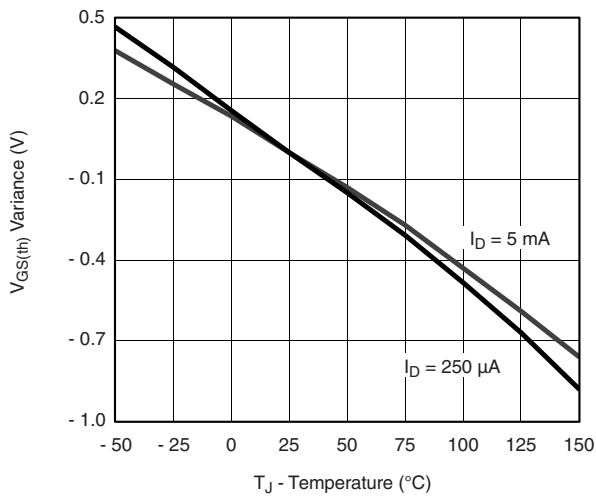
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



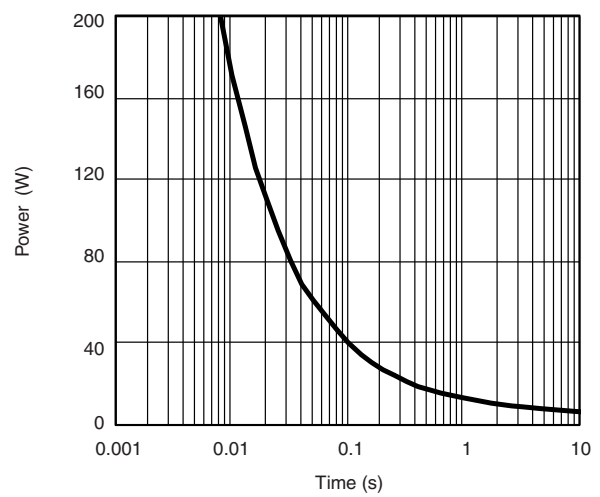
Source-Drain Diode Forward Voltage



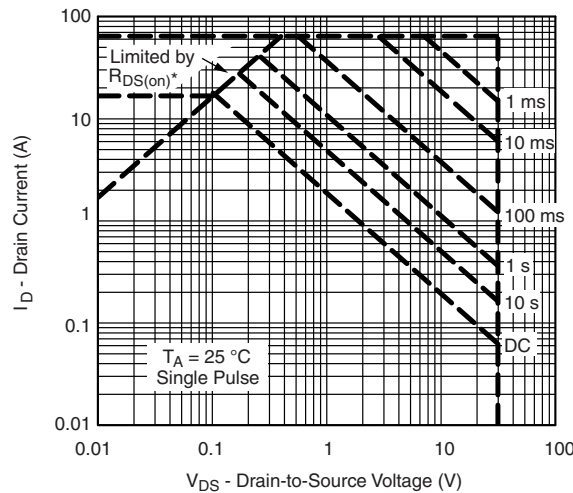
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



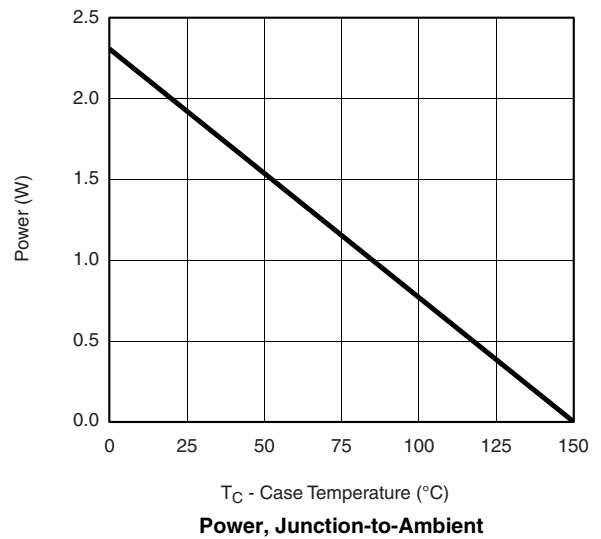
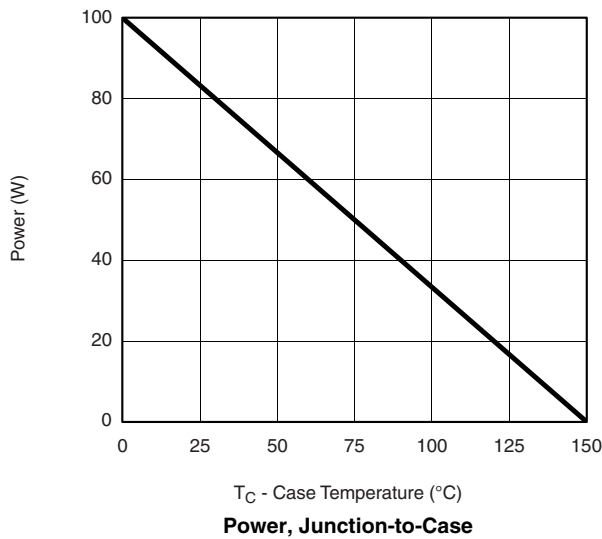
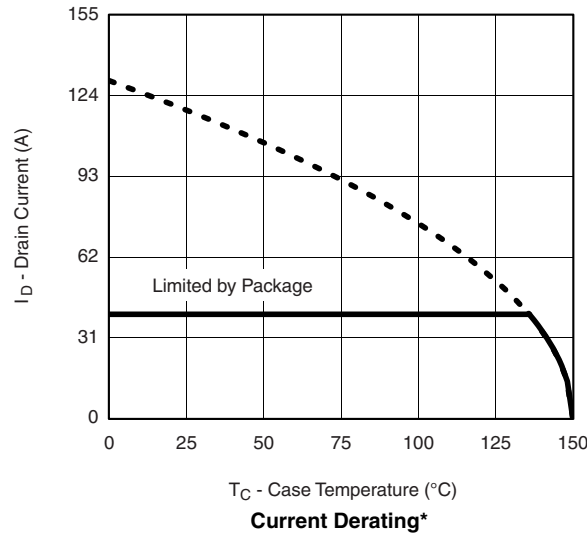
Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

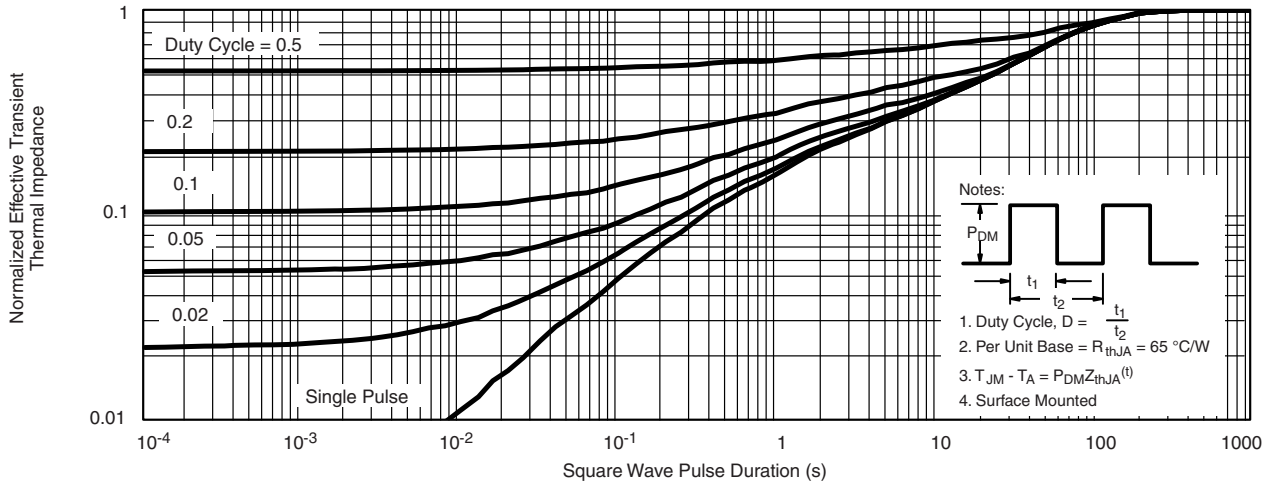
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

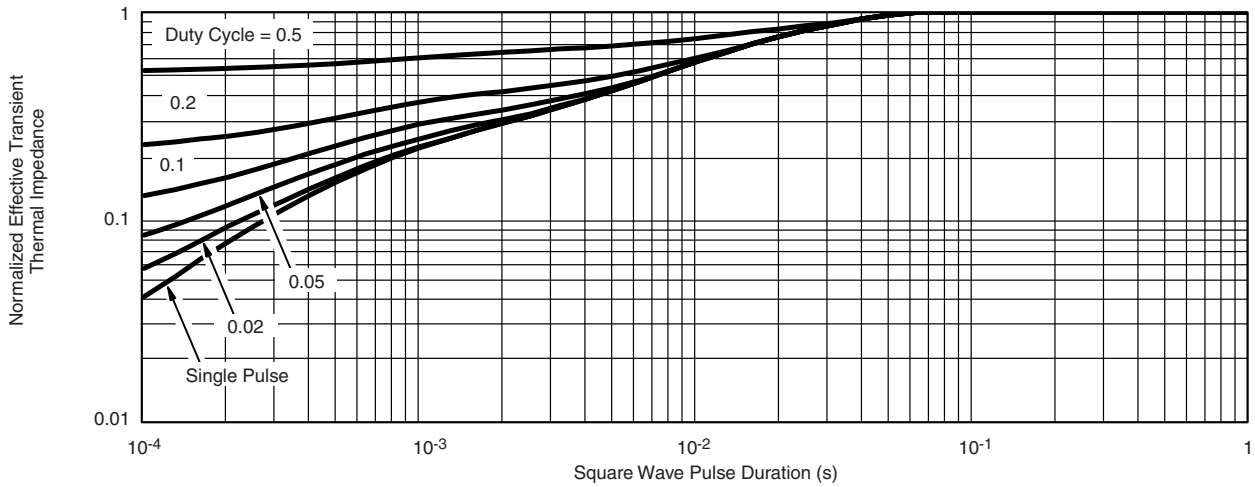


* The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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